

## AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph at page 10, line 14, with the following rewritten paragraph:

In the case that protective layer 6 is formed by the vacuum deposition method, front glass substrate 2 is heated at 200°C-400°C, and a deposition chamber is depressurized at  $3 \times 10^{-4}$  Pa by an exhausting apparatus. A predetermined number of evaporation sources of hollow cathodes and an electron beam is set in the chamber as to evaporate MgO and the additive added to MgO. Then, these materials are deposited on dielectric layer 6 5 with using reaction gas, such as oxygen gas ( $O_2$  gas). According to the embodiment, while  $O_2$  gas is put into the deposition chamber depressurized within a range from 0.01 Pa to 1.0 Pa by the exhausting system. Then, MgO and the additive, i.e., 50ppm by weight to 7000ppm of magnesium carbide, such as  $MgC_2$ ,  $Mg_2C_3$ , or  $Mg_3C_4$  are evaporated by the electron beam or the evaporation source of the hollow cathode, thereby providing protective layer 6 on dielectric layer 5.